L Number	Hits	Search Text	DB	Time stamp
1	2	("6674667").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:46
4	13763	metal adj oxide adj semiconductor adj field adj effect adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
5	3	apply$6 adj2 third adj voltage near1 potential adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
9	6	(apply$6 adj2 first adj voltage near1 potential adj3 source) or (apply$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
10	5	((apply$6 adj2 first adj voltage near1 potential adj3 source) or (apply$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
11	2	(((apply$6 adj2 first adj voltage near1 potential adj3 source) or (apply$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel) and negative adj gate adj1 potential near3 conduction adj1 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
12	2	(((apply$6 adj2 first adj voltage near1 potential adj3 source) or (apply$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel) and negative adj gate adj1 potential	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
13	0	apply$6 adj2 negative adj3 voltage near1 potential adj3 gate near5 MOSFEt	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
16	862	apply$6 adj2 negative adj3 voltage adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
17	5020	apply$6 adj2 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
18	5020	apply$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
19	1107	(apply$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate) and MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
20	269	apply$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
21	108	apply$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
2	3	"20020110033" or (("6674667").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
3	2	"20020110033"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
6	3	apply$6 adj2 third adj3 voltage near1 potential adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48

7	6	apply$6 adj2 first adj voltage near1 potential adj3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
8	7	apply$6 adj2 second adj voltage near1 potential adj3 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
14	6	apply$6 adj2 negative adj3 voltage near1 potential adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
15	18	(("4,051,354") or ("5,324,681") or ("5,327,380") or ("5,493,141") or ("5,764,096") or ("5,768,192") or ("5,781,477") or ("6,038,168") or ("6,229,733")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
22	161	apply$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	USPAT	2004/07/26 07:48
23	153	apply$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj1 voltage adj3 gate near5 mosfet	USPAT	2004/07/26 07:48
24	153	apply adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj1 voltage adj3 gate near5 mosfet	USPAT	2004/07/26 07:48
25	153	appl$ adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj1 voltage adj3 gate near5 mosfet	USPAT	2004/07/26 07:48
26	31	(appl$ adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj1 voltage adj3 gate near5 mosfet) and negative adj1 voltage	USPAT	2004/07/26 07:48
27	7	ONO adj anti adj1 fuse	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
28	2	"20030235077"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
29	2	"20030235085"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
30	2	("5324681").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
31	2	("5764096").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
32	29	metal adj oxide adj semiconductor adj field adj effect adj transistor near3 switch$6 adj element	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:48
33	37	(("3,992,701") or ("4,761,768") or ("4,766,569") or ("5,172,204") or ("5,414,658") or ("5,544,118") or ("5,763,912") or ("5,828,099") or ("5,851,893") or ("5,867,425") or ("5,978,273") or ("6,180,957") or ("6,243,298") or ("6,272,042") or ("6,452,835") or ("6,456,535") or ("6,504,762") or ("6,510,086") or ("6,664,601")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:52
34	19	(("3,992,701") or ("4,761,768") or ("4,766,569") or ("5,172,204") or ("5,414,658") or ("5,544,118") or ("5,763,912") or ("5,828,099") or ("5,851,893") or ("5,867,425") or ("5,978,273") or ("6,180,957") or ("6,243,298") or ("6,272,042") or ("6,452,835") or ("6,456,535") or ("6,504,762") or ("6,510,086") or ("6,664,601")).PN.	USPAT	2004/07/26 07:54
35	1	("6700821").PN.	USPAT	2004/07/26 07:54

37	2	("6521958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 07:55
38	2	("20040114433").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 07:55
36	3	("6700821").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 07:57